NSN 5962-01-381-8265

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-381-8265
Maximum Power Dissipation Rating:
1.2 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Used on (07187) 8515143-910
Features Provided:
Programmed and tested to mil-std-883
Inclosure Configuration:
Leaded chip carrier
Output Logic Form:
Bipolar metal-oxide semiconductor
Input Circuit Pattern:
16 input
Case Outline Source And Designator:
C-2 mil-m-38510
Terminal Surface Treatment:
Solder
Product Name:
Programmed/16-input 8-output registered and-or gate array
Voltage Rating And Type Per Characteristic:
4.5 volts applied and 5.5 volts applied
Memory Device Type:
Pal
Hybrid Technology Type:
Monolithic
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And
07187-tt8518595-101 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
20 printed circuit
Specification Data:
67268-5962-85155182a government standard
Departure From Cited Document:
Modified by programming
Shelf Life:
N/a

Vec - demil/mli

Unit Of Measure:

Demilitarization:

NSN 5962-01-381-8265

Memory Microcircuit - Page 2 of 2



Fiig:

A458a0